

**REMARKS**

Reconsideration of the application in view of the above amendments and the following remarks is respectfully requested.

The Examiner requires that the title of the invention be conformed to the present invention and that the cross-reference to the related document be inserted in the specification. The Specification has been so amended.

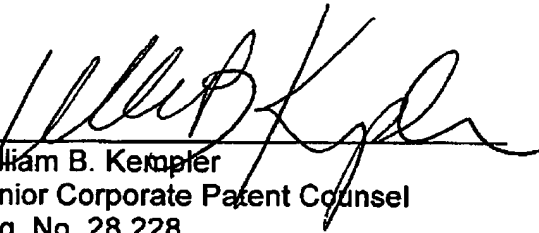
The Examiner rejects claims 8, 9 and 16-23 under 35 U.S.C. § 102(e) as being anticipated by Giust et al.

This rejection is respectfully traversed. The protrusion formed in Giust is formed by etching the dielectric material, forming a metal layer and then flattening the metal layer, such as by chemical-mechanical polishing (CMP). Thus, this process requires different steps from the process used to manufacture other the parts of the integrated circuit, thereby adding to the cost of manufacture and decreasing the yield thereof.

In sharp contrast, the present invention utilizes transistor forming techniques in which a diffusion is placed into the semiconductor substrate. As known to those skilled in the art, the oxide layer is removed or thinned in the area where the diffusion is to take place, and then a new oxide layer is grown on the surface of the integrated circuit, so that the next layer of the device can be formed. This forms the step shown in FIGURE 1 of the present application. In view of the fact that these steps are required for the formation of other transistor devices on the integrated circuit, no new process steps are added, which does not increase the cost or reduce the yield of the device. Independent Claim 8 has been amended in this respect.

Accordingly, Applicants believe the Application, as amended, is in condition for allowance, and such action is respectfully requested.

Respectfully submitted,  
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